

Pb Free Plating Product

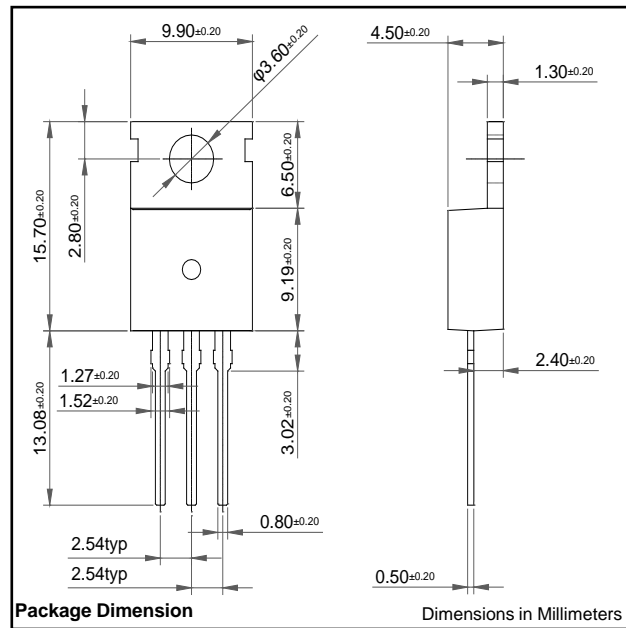
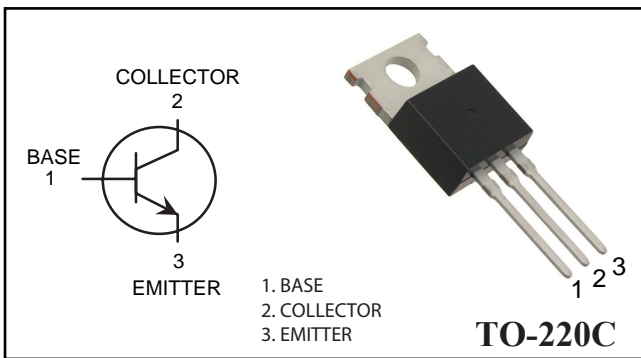
2SD1163/2SD1163A



NPN Silicon Epitaxial Power Transistor

FEATURES:

- * Medium Power Linear Switching Applications
- * Low collector saturation voltage
- TV horizontal deflection output



Absolute maximum ratings (Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2SD1163	300	V
		2SD1163A	350	
V _{CEO}	Collector-emitter voltage	2SD1163	120	V
		2SD1163A	150	
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		7	A
I _{CM}	Collector current-peak		10	A
I _{C(surge)}	Collector current-surge		20	A
P _C	Collector power dissipation	T _C =25	40	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	2SD1163	I _C =10mA ; R _{BE} =	120			V
		2SD1163A		150			
V _{(BR)EBO}	Emitter-base breakdown voltage		I _E =10mA ; I _C =0	6			V
V _{CEsat}	Collector-emitter saturation voltage	2SD1163	I _C =5A, I _B =0.5A			2.0	V
		2SD1163A		1.0			
V _{BEsat}	Base-emitter saturation voltage		I _C =5A, I _B =0.5A			1.2	V
I _{CBO}	Collector cut-off current	2SD1163	V _{CB} =300V; I _E =0			5	mA
		2SD1163A	V _{CB} =350V; I _E =0			5	mA
h _{FE}	DC current gain		I _C =5A ; V _{CE} =5V	25			

Switching times

t _f	Fall time	I _{CM} =3.5A; I _{B1} =0.45A			0.5	μs
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